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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Matthias Passlack et al.

) Patent No.: 6,756,320 B2

Application No.: 10/051,494

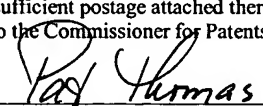
) Issue Date: June 29, 2004

Filed: January 18, 2002

) Docket No.: SC11692ZP

Title: ARTICLE COMPRISING AN OXIDE LAYER ON A GAAS-BASED
SEMICONDUCTOR STRUCTURECertificate of MailingDate of deposit: 4-3-06

I hereby certify that this paper is being deposited with the United States Postal Service on the date indicated above, as first-class mail, with sufficient postage attached thereto, in an envelope addressed to the Commissioner for Patents, Alexandria, VA 22313.



Signature of Person Mailing PaperPat Thomas
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Commissioner for Patents
Alexandria, VA 22313**Certificate**
APR 11 2006
of CorrectionSUBMISSION OF CERTIFICATE OF CORRECTION

Dear Commissioner:

Enclosed, in duplicate, is a Certificate of Correction for errors in the subject patent.
Please enter these corrections.

Since the errors appear to be on the part of the United States Patent Office, there should be no charge.

Respectfully submitted,

3/31/06
Date
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PTO/SB/ 44 (04-05)

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CERTIFICATE OF CORRECTION**

Page 1 of 1

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DATE: June 29, 2004
INVENTOR(S): Matthias Passlack et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

In Column 6, Line 33, change "Ga²O³" to -Ga₂O₃- -

In Column 6, Line 34, after "material" insert - -of Ga-Gd oxide- -

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